- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

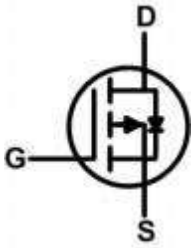
BVDSS	RDSON	ID
-60V	70mΩ	-8.0A

Description

The **TCS1568** is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The **TCS1568** meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

SOP8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ -10V[1]	-8.0	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ -10V[1]	-6.2	A
I_{DM}	Pulsed Drain Current[2]	-16.2	A
EAS	Single Pulse Avalanche Energy[3]	69.7	mJ
I_{AS}	Avalanche Current	44.4	A
P_D@T_A=25℃	Total Power Dissipation[4]	6.1	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	85	℃/ W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	36	℃/ W